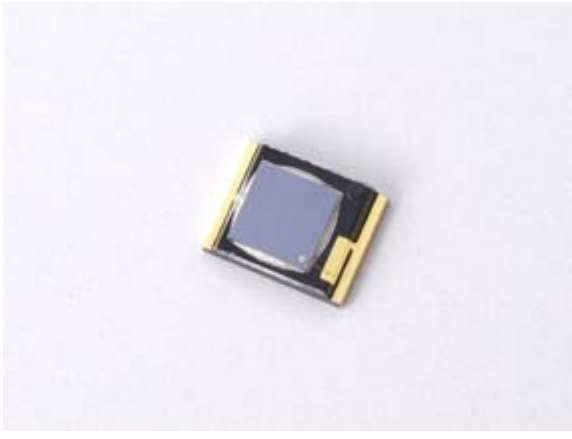


Si Photodiode KPD30S

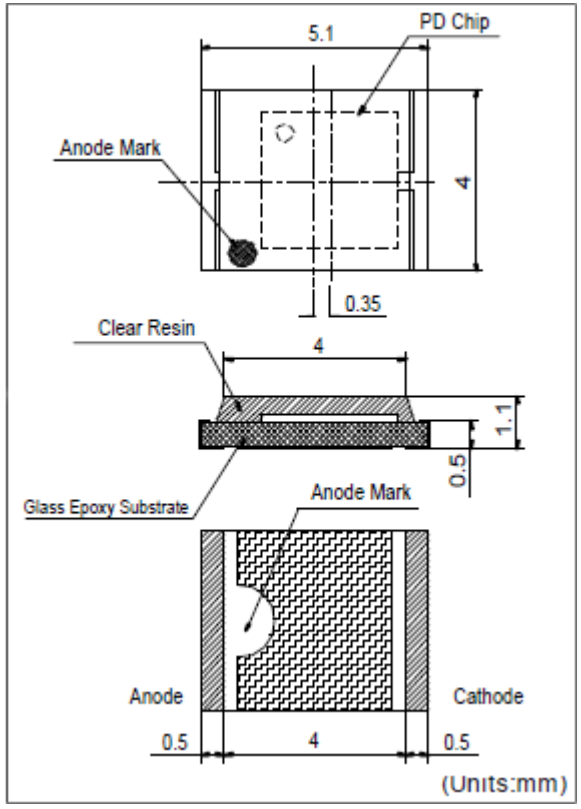


Features

- Transparent epoxy mold
- High sensitivity

Applications

- Optical switches
- Optical encoders
- Pulse detectors
- Sensors and industrial controls



Maximum ratings

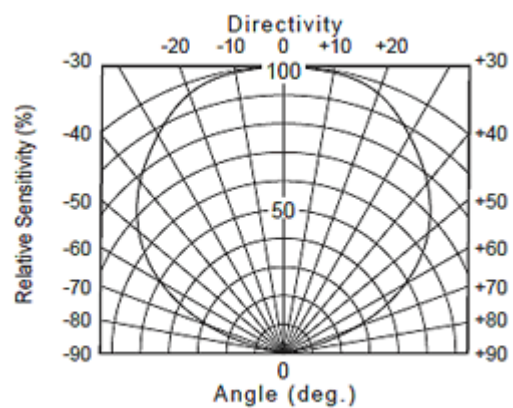
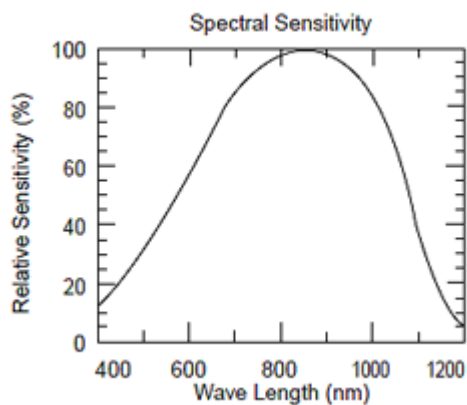
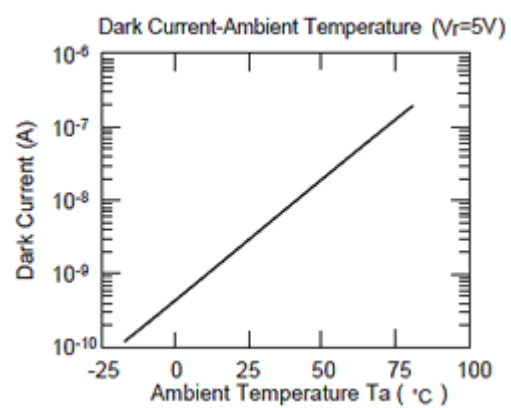
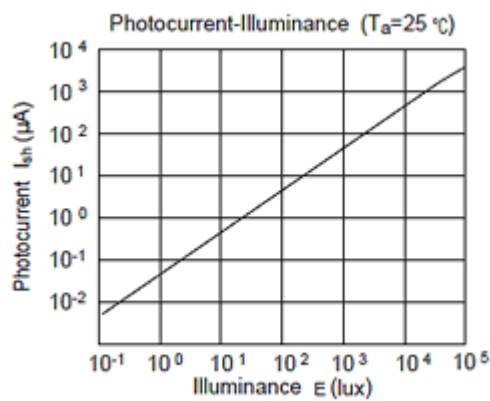
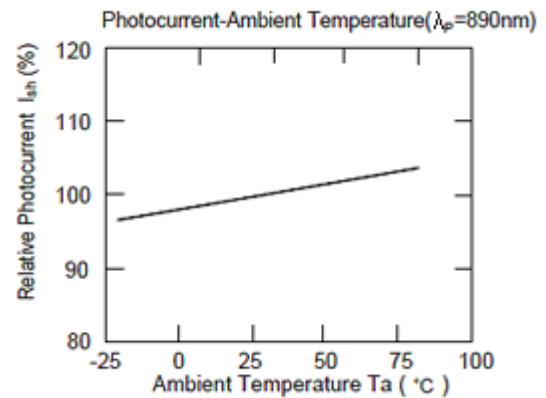
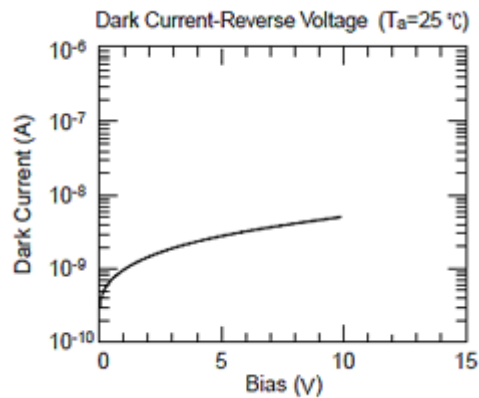
Item	Symbol	Value	Units
Reverse Voltage	V_R	5	V
Reverse Current	I_R	1	mA
Forward Current	I_F	10	mA
Operating Temperature	T_{op}	-25 ~ +80	° C
Storage Temperature	T_{stg}	-25 ~ +100	° C
Soldering Temper ature	T_{sol}	260 (3sec max)	° C

Characteristics (Ta=25°C unless otherwise noted.)

Parameter	Symbol	Min.	Typ.	Max.	Units	Test Conditions
Active Area	S	2.59x 2.59			mm	
Operating Voltage	V_{RO}			5	V	
Sensitive Wavelength	λ	400	850 (λ_P)	1000	mm	λ_P = Peak wavelength
Open Circuit Voltage	V_{op}		350		mV	1000lux (@2856K)

Short Circuit Current	I_{sh}		68		μA	
Dark Current	I_d			30	nA	$V_R = 5\text{V}$
Capacitance	C_t		30		pF	$V_R = 5\text{V}, f = 1\text{MHz}$
Half angle	$\Delta \theta$		± 60		deg	

Typical Characteristics



KYOSEMI CORP.

China representative: CTW Technology Co., Ltd. <http://www.ctwtek.com>